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**(APD/19760101->19980609 AND (DRAM AND "redundant memory")):** 390 patents.

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	<b>PAT. NO.</b>	<b>Title</b>
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9	<a href="#">6,317,370</a>	<a href="#">Timing fuse option for row repair</a>
10	<a href="#">6,307,273</a>	<a href="#">High contrast, low noise alignment mark for laser trimming of redundant memory arrays</a>
11	<a href="#">6,288,421</a>	<a href="#">Semiconductor memory circuitry including die sites for 16M to 17M memory cells in an 8" wafer</a>
12	<a href="#">6,272,577</a>	<a href="#">Data processing system with master and slave devices and asymmetric signal swing bus</a>
13	<a href="#">6,266,753</a>	<a href="#">Memory manager for multi-media apparatus and method therefor</a>
14	<a href="#">6,252,281</a>	<a href="#">Semiconductor device having an SOI substrate</a>
15	<a href="#">6,243,829</a>	<a href="#">Memory controller supporting redundant synchronous memories</a>
16	<a href="#">6,223,248</a>	<a href="#">Circuits systems and methods for re-mapping memory row redundancy during two cycle cache access</a>

- 17 [6,208,567](#) **T** [Semiconductor device capable of cutting off a leakage current in a defective array section](#)
- 18 [6,208,545](#) **T** [Three dimensional structure memory](#)
- 19 [6,205,514](#) **T** [Synchronous SRAM having global write enable](#)
- 20 [6,194,738](#) **T** [Method and apparatus for storage of test results within an integrated circuit](#)
- 21 [6,182,257](#) **T** [BIST memory test system](#)
- 22 [6,178,549](#) **T** [Memory writer with deflective memory-cell handling capability](#)
- 23 [6,154,851](#) **T** [Memory repair](#)
- 24 [6,149,316](#) **T** [Flash EEprom system](#)
- 25 [6,141,768](#) **T** [Self-corrective memory system and method](#)
- 26 [6,134,681](#) **T** [Semiconductor memory device with spare memory cell](#)
- 27 [6,133,640](#) **T** [Three-dimensional structure memory](#)
- 28 [6,130,837](#) **T** [Storage device employing a flash memory](#)
- 29 [6,130,468](#) **T** [Fuse, memory incorporating same and method](#)
- 30 [6,130,442](#) **T** [Memory chip containing a non-volatile memory register for permanently storing information about the quality of the device and test method therefor](#)
- 31 [6,122,213](#) **T** [Device and method for repairing a memory array by storing each bit in multiple memory cells in the array](#)
- 32 [6,115,828](#) **T** [Method of replacing failed memory cells in semiconductor memory device](#)
- 33 [6,115,299](#) **T** [Device and method for repairing a memory array by storing each bit in multiple memory cells in the array](#)
- 34 [6,105,152](#) **T** [Devices and methods for testing cell margin of memory devices](#)
- 35 [6,104,645](#) **T** [High speed global row redundancy system](#)
- 36 [6,097,643](#) **T** [Semiconductor storage apparatus and method of manufacturing of the same](#)
- 37 [6,093,933](#) **T** [Method and apparatus for fabricating electronic device](#)
- 38 [6,081,463](#) **T** [Semiconductor memory remapping](#)
- 39 [6,078,534](#) **T** [Semiconductor memory having redundancy circuit](#)
- 40 [6,073,258](#) **T** [Method and device for performing two dimensional redundancy calculations on embedded memories avoiding fail data collection](#)
- 41 [6,073,251](#) **T** [Fault-tolerant computer system with online recovery and reintegration of redundant components](#)
- 42 [6,069,064](#) **T** [Method for forming a junctionless antifuse](#)
- 43 [6,066,886](#) **T** [Semiconductor wafer in which redundant memory portion is shared by two neighboring semiconductor memory portions and is connected to the semiconductor memory portions](#)
- 44 [6,066,539](#) **T** [Honeycomb capacitor and method of fabrication](#)
- 45 [6,055,611](#) **T** [Method and apparatus for enabling redundant memory](#)
- 46 [6,055,204](#) **T** [Circuits, systems, and methods for re-mapping memory column redundancy](#)
- 47 [6,055,196](#) **T** [Semiconductor device with increased replacement efficiency by redundant memory cell arrays](#)
- 48 [6,049,505](#) **T** [Method and apparatus for generating memory addresses for testing memory devices](#)
- 49 [6,046,945](#) **T** [DRAM repair apparatus and method](#)

50 [6,044,029](#)  [Device and method for repairing a memory array by storing each bit in multiple memory cells in the array](#)

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